

2SB0976 (2SB976)

Silicon PNP epitaxial planar type

For low-frequency output amplification

For DC-DC converter

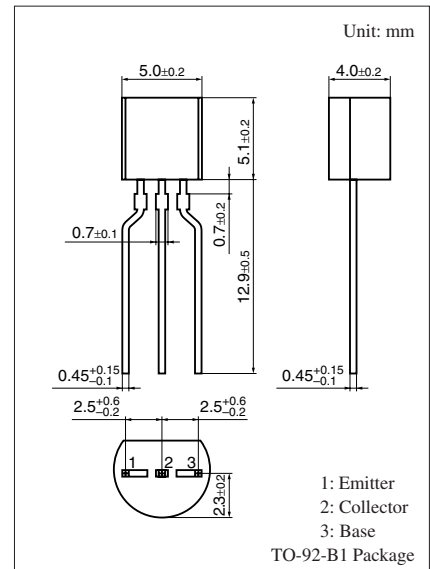
For stroboscope

■ Features

- Low collector-emitter saturation voltage $V_{CE(sat)}$
- Large collector current I_C

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	V_{CBO}	-27	V
Collector-emitter voltage (Base open)	V_{CEO}	-18	V
Emitter-base voltage (Collector open)	V_{EBO}	-7	V
Collector current	I_C	-5	A
Peak collector current	I_{CP}	-8	A
Collector power dissipation	P_C	0.75	W
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$



■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-emitter voltage (Base open)	V_{CEO}	$I_C = -1 \text{ mA}, I_B = 0$	-18			V
Emitter-base voltage (Collector open)	V_{EBO}	$I_E = -10 \mu\text{A}, I_C = 0$	-7			V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = -10 \text{ V}, I_E = 0$			-100	nA
Emitter-base cutoff current (Collector open)	I_{EBO}	$V_{EB} = -5 \text{ V}, I_C = 0$			-1	μA
Forward current transfer ratio ^{*1, 2}	h_{FE}	$V_{CE} = -2 \text{ V}, I_C = -2 \text{ A}$	125		625	—
Collector-emitter saturation voltage ^{*1}	$V_{CE(sat)}$	$I_C = -3 \text{ A}, I_B = -0.1 \text{ A}$		-0.4	-1.0	V
Transition frequency	f_T	$V_{CB} = -6 \text{ V}, I_E = 50 \text{ mA}, f = 200 \text{ MHz}$		120		MHz
Collector output capacitance (Common base, input open circuited)	C_{ob}	$V_{CB} = -20 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		60		pF

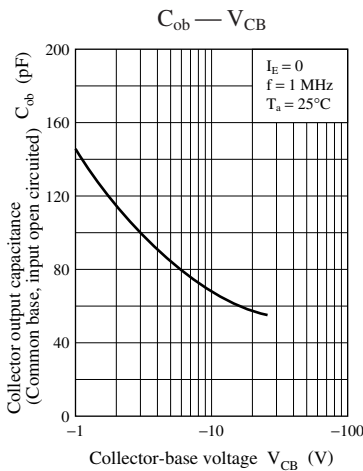
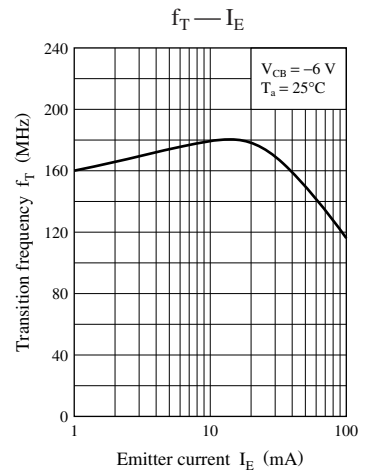
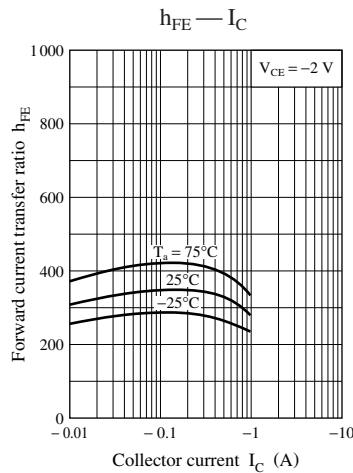
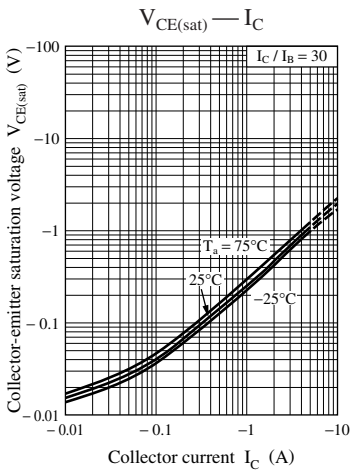
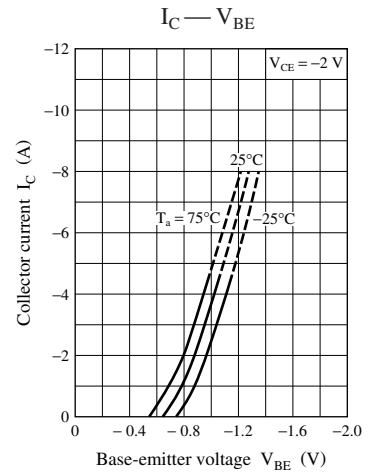
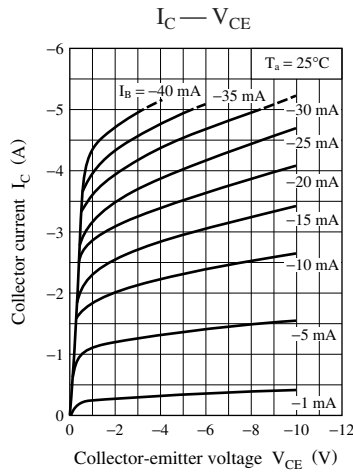
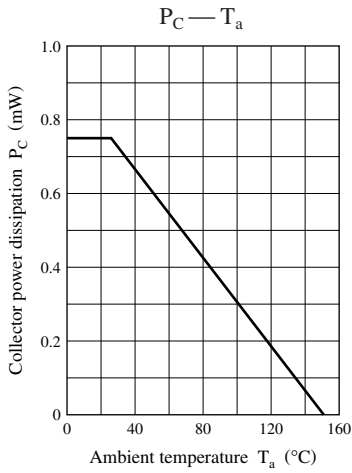
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. *1: Pulse measurement

*2: Rank classification

Rank	Q	R
h_{FE}	125 to 205	180 to 625

Note) The part number in the parenthesis shows conventional part number.



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